	Search Text	DBs
1		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
2	(("5698869") or ("5728592")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
3	("348/46")).CCLS.) and	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
4	((thin adj film adj transistor) or TFT) and ((anodically or anodizing or anode) near (oxidized or oxidizing or oxidized))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
5	(((thin adj film adj transistor) or TFT) and ((anodically or anodizing or anode) near (oxidized or oxidizing or oxidized))) and (angled or tapered or tappered)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
6	((photoresist or resist or (photo adj resist)) near (bake or baked)) same temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
7	<pre>(((photoresist or resist or (photo adj resist)) near (bake or baked)) same temperature) and (TFT or (thin adj film adj transitor))</pre>	EPO; JPO;. `
8	anodically adj oxidizing	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
9	("5202274").PN.	USPAT
10	5202274.URPN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
11	(anodically adj oxidizing) near (advantage or advantages)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
12	(anodically adj oxidizing) same (advantage or advantages)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB